

ABSTRACT

A method for reducing hot carrier reliability problems within an integrated circuit device. The method includes forming a shallow trench isolation structure incorporated with the device by filling a trench with a photoresist plug and
5 removing a portion of the photoresist plug to a level below the depth of a channel also incorporated with the device. A nitride liner disposed within the trench under the photoresist plug is then recessed to a level substantially equal to the level of the photoresist material, which is then removed. The method further includes the deposition of oxide fill within the trench, thereby encapsulating the recessed nitride
10 liner.

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